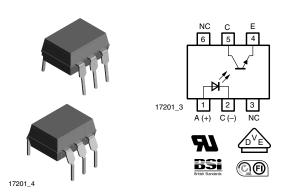
Vishay Semiconductors



Optocoupler, Phototransistor Output



DESCRIPTION

The TCDT1100, TCDT1100G series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6 pin plastic dual inline package. The base of the phototransistor is not connected providing noise immunity.

VDE STANDARDS

These couplers perform safety functions according to the following equipment standards:

- DIN EN 60747-5-5 (VDE0884)
 Optocoupler for electrical safety requirements
- IEC 60950/EN 60950
 Office machines (applied for reinforced isolation for mains voltage ≤ 400 V_{RMS})
- VDE0804
 Telecommunication apparatus and data processing
- IEC 60065
 Safety for mains-operated electronic and related household apparatus

FEATURES

- Isolation test voltage 5000 V_{RMS}
- · High common mode rejection
- No base terminal connection for improved noise immunity



• CTR offered in 4 groups

- Thickness though insulation ≥ 0.4 mm
- Creepage current resistance according to VDE0303/ IEC 60112 comparative tracking index: CTI ≥ 275
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- Switch-mode power supplies
- · Line receiver
- · Computer peripheral interface
- · Microprocessor system interface
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
 - for appl. class I IV at mains voltage ≤ 300 V
 - for appl. class I III at mains voltage $\leq 600~V$ according to DIN EN 60747-5-5

AGENCY APPROVALS

- UL1577, file no. E52744, double protection
- BSI IEC 60950; IEC 60065 pending
- DIN EN 60747-5-5 (VDE0884)
- FIMKO

ORDER INFORMATION	
PART	REMARKS
TCDT1100	CTR > 40 %, DIP-6
TCDT1101	CTR 40 % to 80 %, DIP-6
TCDT1102	CTR 63 % to 125 %, DIP-6
TCDT1103	CTR 100 % to 200 %, DIP-6
TCDT1100G	CTR > 40 %, DIP-6, 400 mil
TCDT1101G	CTR 40 % to 80 %, DIP-6, 400 mil
TCDT1102G	CTR 63 % to 125 %, DIP-6, 400 mil
TCDT1103G	CTR 100 % to 200 %, DIP-6, 400 mil

Note

• G = leadform 10.16 mm; G is not marked on the body.



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ABSOLUTE MAXIMUM RATINGS ⁽¹⁾ (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT	<u> </u>						
Reverse voltage		V _R	5	V			
Forward current		I _F	60	mA			
Forward surge current	t _p ≤ 10 μs	I _{FSM}	3	А			
Power dissipation		P _{diss}	70	mW			
Junction temperature		Tj	125	°C			
OUTPUT			<u>. </u>				
Collector emitter voltage		V_{CEO}	32	V			
Emitter collector voltage		V _{ECO}	7	V			
Collector current		I _C	50	mA			
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA			
Power dissipation		P _{diss}	70	mW			
Junction temperature		T _j	125	°C			
COUPLER			<u>. </u>				
Isolation test voltage (RMS)		V _{ISO}	5000	V _{RMS}			
Total power dissipation		P _{tot}	200	mW			
Ambient temperature range		T _{amb}	- 55 to + 110	°C			
Storage temperature range		T _{stg}	- 55 to + 125	°C			
Soldering temperature (2)	2 mm from case, t ≤ 10 s	T _{sld}	260	°C			

Notes

⁽²⁾ Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTCS (1) (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	I _F = 50 mA	V _F		1.25	1.6	V		
Junction capacitance	V _R = 0, f = 1 MHz	C _j		50		pF		
OUTPUT	·							
Collector emitter voltage	I _C = 1 mA	V _{CEO}	32			V		
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7			V		
Collector ermitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0, E = 0$	I _{CEO}		200		nA		
COUPLER	<u> </u>							
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V		
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA},$ $R_L = 100 \Omega$	f _c		110		kHz		
Coupling capacitance	f = 1 MHz	C _k		0.6		pF		

Note

⁽¹⁾ Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽¹⁾ Minimum and maximum values are testing requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

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CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
		TCDT1100	CTR	40			%	
		TCDT1100G CTR 40	40 40		%			
I _C /I _F		TCDT1101	CTR	40		80	%	
	V - 5 V I - 10 mA	TCDT1101G	CTR				%	
	$V_{CE} = 5 \text{ V}, I_{F} = 10 \text{ mA}$	TCDT1102	CTR	63		125	%	
		TCDT1102G	CTR				%	
		TCDT1103	CTR	100)	200	%	
		TCDT1103G	CTR				%	

MAXIMUM SAFETY RATINGS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT	INPUT							
Forward current		I _F			130	mA		
OUTPUT								
Power dissipation		P _{diss}			265	mW		
COUPLER								
Rated impulse voltage		V _{IOTM}			6	kV		
Safety temperature		T _{si}			150	°C		

Note

 According to DIN EN 60747-5-5. This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Partial discharge test voltage - routine test	100 %, t _{test} = 1 s	V_{pd}	1.6			kV	
Partial discharge test voltage - lot test (sample test)	t _{Tr} = 60 s, t _{test} = 10 s, (see figure 1)	V_{IOTM}	6			kV	
		V_{pd}	1.3			kV	
Insulation resistance	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω	
	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹			Ω	
	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹			Ω	

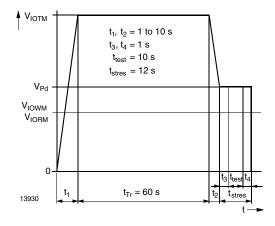


Fig. 1 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-5/DIN EN 60747-; IEC60747



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SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see figure 2)}$	t _d		4		μs	
Rise time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see figure 2)}$	t _r		7		μs	
Fall time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 2)	t _f		6.7		μs	
Storage time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 2)	t _s		0.3		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 2)	t _{on}		11		μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see figure 2)}$	t _{off}		7		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 10 \text{ mA}, R_L = 1 \text{ k}\Omega, \text{ (see figure 3)}$	t _{on}		25		μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 10 \text{ mA}, R_L = 1 \text{ k}\Omega$, (see figure 3)	t _{off}		42.5		μs	

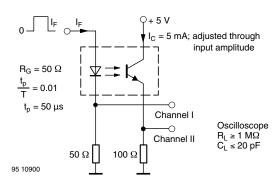


Fig. 2 - Test Circuit, Non-Saturated Operation

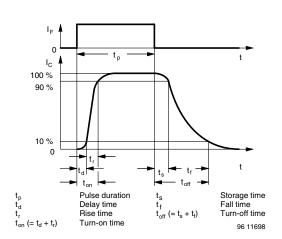


Fig. 4 - Switching Times

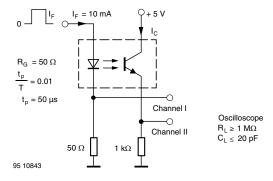


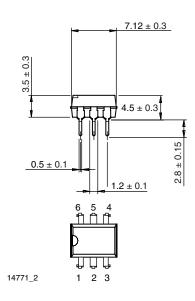
Fig. 3 - Test Circuit, Saturated Operation

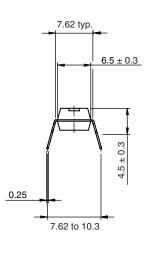
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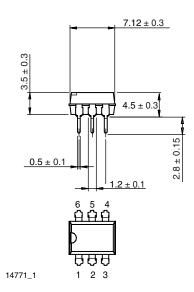
PACKAGE DIMENSIONS in millimeters

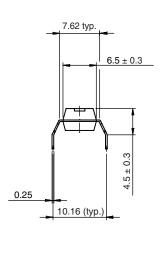
DIP-6



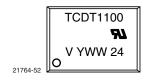


DIP-6, 400 mil





PACKAGE MARKING





Vishay

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